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Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 40 A



PRIMARY CHARACTERISTICS							
I _{T(AV)} 25 A							
V _{DRM} /V _{RRM}	1200 V						
V _{TM}	1.6 V						
I _{GT}	35 mA						
T _J	-40 °C to 140 °C						
Package	3L TO-220AB						
Circuit configuration	Single SCR						

FEATURES

- Designed and qualified according to JEDEC®-JESD 47
- 140 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-40TTS12... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 140 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	25	Δ.						
I _{RMS}		40	A						
V _{RRM} /V _{DRM}		1200	V						
I _{TSM}		350	A						
V _T	T _J = 25 °C	1.6	V						
dV/dt		500	V/µs						
dl/dt		150	A/μs						
T _J		-40 to +140	°C						

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	ο̂ζ						
VS-40TTS12-M3	1200	1200	-25 to +140						



ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS			
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° conduc	tion half sine wave	25			
Maximum RMS on-state current	I _{RMS}			40	Α		
Maximum peak, one-cycle	I	10 ms sine pulse, rated \	V _{RRM} applied	300	A		
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no vol	tage reapplied	350			
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated \	V _{RRM} applied	450	A ² s		
Maximum 1-t for fusing	1-1	10 ms sine pulse, no vol	tage reapplied	630	A-S		
Maximum l ² √t for fusing	l ² √t	t = 0.1 to 10 ms, no volta	age reapplied	6300	A²√s		
Maximum on-state voltage	V_{TM}	80 A, T _J = 25 °C		1.6	V		
Low level value of on-state slope resistance	r _t	T 140.90		11.4	mΩ		
Low level value of threshold voltage	V _{T(TO)}	T _J = 140 °C		0.96	V		
Maximum reverse and direct leakage	1 //	T _J = 25 °C	V Datad V A/	0.5			
current	I _{RRM} /I _{DRM}	T _J = 140 °C	V _R = Rated V _{RRM} /V _{DRM}	12			
Holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		100	mA		
Maximum latching current	lι	Anode supply = 6 V, resistive load, T _J = 25 °C		200			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C, } V_{DRM} = R_g - k = \text{Open}$		500	V/µs		
Maximum rate of rise of turned-on current	dl/dt		-		A/μs		

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P _{GM}		8.0	W				
Maximum average gate power	P _{G(AV)}		2.0	l vv				
Maximum peak positive gate current	+ I _{GM}		1.5	Α				
Maximum peak negative gate voltage	- V _{GM}		10	V				
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	35	mA				
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	1.3	V				
Maximum DC gate voltage not to trigger	V_{GD}	T 140 °C V Poted value	0.2					
Maximum DC gate current not to trigger	I _{GD}	T _J = 140 °C, V _{DRM} = Rated value	1.5	mA				

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T _{.1} = 140 °C	4	μs				
Typical turn-off time	t _q	1j = 140 C	110					

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to 140	°C			
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	0.8				
Maximum thermal resistance, junction to ambient		R_{thJA}		60	°C/W			
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5				
Approximate weight				2	g			
Approximate weight				0.07	OZ.			
Mounting torque	minimum			6 (5)	kgf · cm			
Woulding torque	maximum			12 (10)	(lbf · in)			
Marking device			Case style 3L TO-220AB	40T	ΓS12			

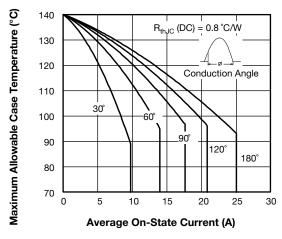


Fig. 1 - Current Rating Characteristics

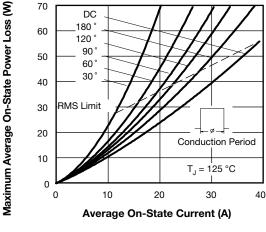


Fig. 4 - On-State Power Loss Characteristics

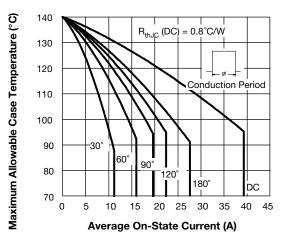


Fig. 2 - Current Rating Characteristics

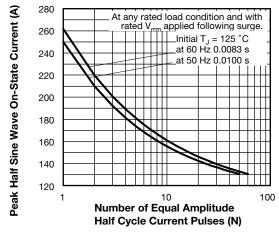


Fig. 5 - Maximum Non-Repetitive Surge Current

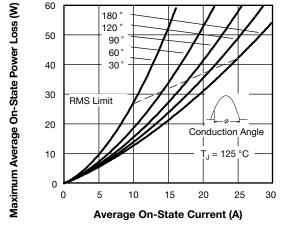


Fig. 3 - On-State Power Loss Characteristics

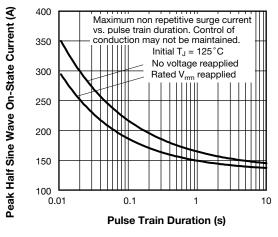


Fig. 6 - Maximum Non-Repetitive Surge Current



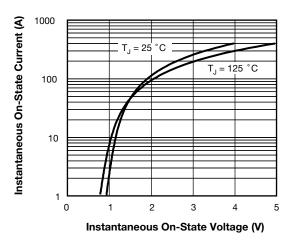


Fig. 7 - On-State Voltage Drop Characteristics

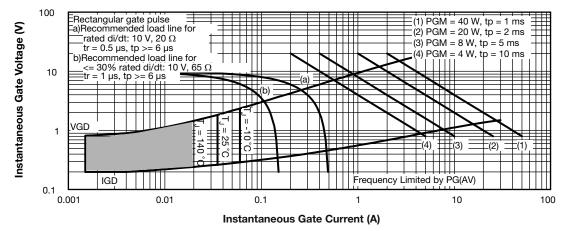


Fig. 8 - Gate Characteristics

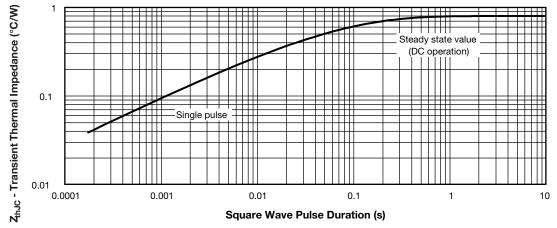
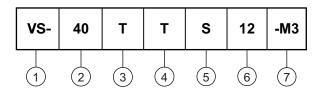


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating, RMS value

3 - Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage rating (12 = 1200 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

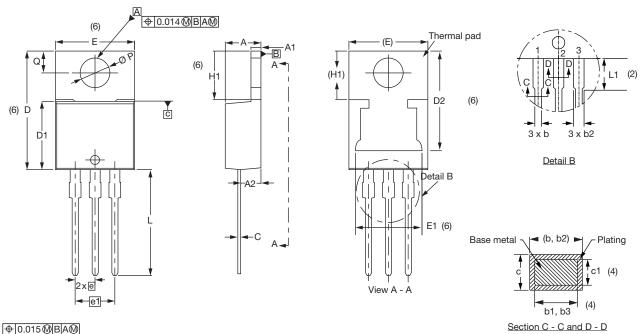
ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-40TTS12-M3	50	1000	Antistatic plastic tubes					

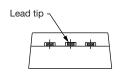
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95028



3L TO-220AB

DIMENSIONS in millimeters and inches





Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIMETERS		INC	INCHES NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355								

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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